Document Number: ITGH09600D4C Preliminary Datasheet V1.0

600W, 28V High Power RF LDMOS FETs

Description

The ITGH09600D4C is a 600W capable, internally matched, **single ended**, 28V LDMOS Designed for multiple application up to 600MHz, especially ISM and RF Energy at 433MHz etc It can be configured as Class AB or Class C for CW or pulsed CW

Please notice both leads at input and output are internally connected

•Typical 433MHz CW Performance (on Innogration fixture with device soldered)

Vds=28V, Vgs=2V

Freq	P1dB	P1dB	P1dB	P1dB	P3dB	P3dB	P3dB
(MHz)	(dBm)	(W)	Eff(%)	Gain(dB)	(dBm)	(W)	Eff(%)
433	57.17	521.7	69.2	22.73	57.91	618.2	71.2

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Internally Matched for Ease of Use
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Excellent thermal stability, low HCI drift
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Table 1. Maximum Ratings

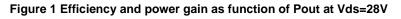
Rating		nbol	Value			Unit
DrainSource Voltage	V	_{bss} 65			Vdc	
GateSource Voltage	V	V _{GS} -10 to +10			Vdc	
Operating Voltage	V	V _{DD} +32			Vdc	
Storage Temperature Range		stg	-65 to +150			°C
Case Operating Temperature		c	+150			°C
Operating Junction Temperature	Т	- J	+225			°C
Fable 2. Thermal Characteristics		·			·	
Characteristic	Syn	nbol	Value			Unit
Thermal Resistance, Junction to Case		10	0.15			°C/W
Tcase= 25°C, DC Power supply		JC	0.15			°C/W
Table 3. ESD Protection Characteristics						
Test Methodology	Class					
Human Body Model (per JESD22A114)		Class 2				
Fable 4. Electrical Characteristics (TA = 25 C unless oth	erwise n	oted)				
Characteristic		Symbol	Min	Тур	Max	Unit
OC Characteristics						
Drain-Source Breakdown Voltage			05			V
$(V_{GS}=0V; I_D=100uA)$		V _{DSS}	65			V
Zero Gate Voltage Drain Leakage Current		I _{DSS}			10	μA



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$(V_{DS} = 28 \text{ V}, V_{GS} = 0 \text{ V})$					
GateSource Leakage Current	I _{GSS}			1	A
$(V_{GS} = 6 V, V_{DS} = 0 V)$					μΑ
Gate Threshold Voltage	$V_{\text{GS}}(\text{th})$		1.75		V
$(V_{DS} = 28V, I_{D} = 600 \text{ uA})$					
Gate Quiescent Voltage	N/		2.5		V
(V_{DD} = 28V, I_{DQ} = 500 mA, Measured in Functional Test)	$V_{GS(Q)}$		2.5		V
Load Mismatch (In Innogration Test Fixture, 50 ohm system): V _{DD} = 28 Vdc, I _{DQ} =100 mA, f = 433MHz					
VSWR 10:1 at 600W pulse CW Output Power No Device Degradation					

433MHz



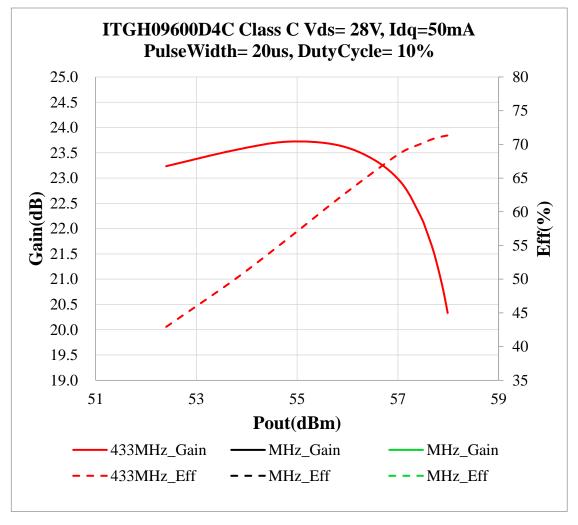


Figure 2: Network analyzer output, S11 and S21

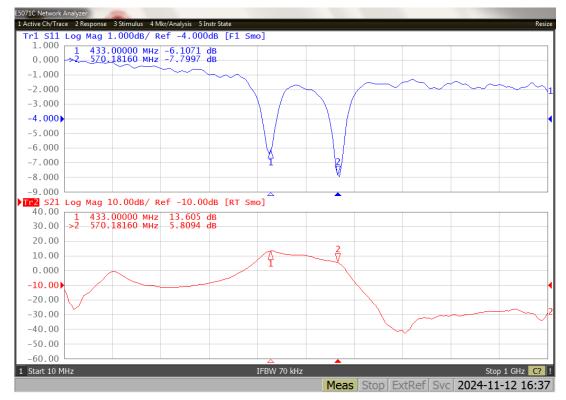
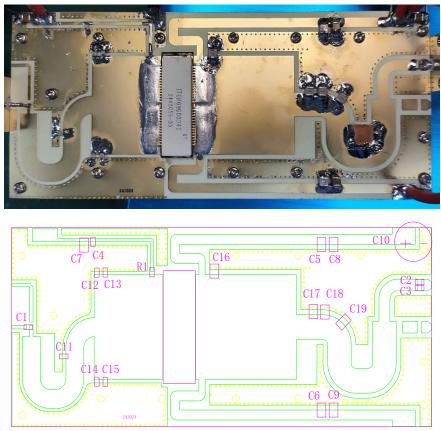


Figure 3: Layout picture (original Gerber file upon request)



PCB: RO4350B 20mils

Table 5. List of components

Designator	Footprint	Comment	Quantity
C1	0603/0805	10 pF	1
C2, C3	0805	82 pF	2
C4	0603/0805	150 pF	1
C5, C6	1210	150 pF	2
C7, C8, C9	1210	10uF/100V	3
C10		1000uF/63V	1
C11, C12, C13, C14, C15	0603/0805	30 pF	5
C16, C19	1210	15 pF	2
C17, C18	1210	18 pF	2
R1	0603/0805	10 Ω	1

Earless Flanged Plastic Air Cavity Package; 4 leads

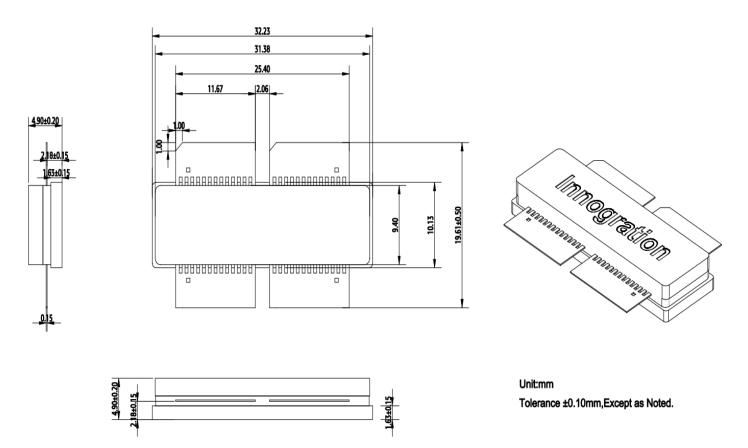


Table 5. Document revision history

Date	Revision	Datasheet Status
2024/11/13	V1	Preliminary Datasheet Creation

Application data based on LSM-24-23

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